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PATENT

OIPE JC34 APR 28 2003 PATENT & TRADEMARK OFFICE

Docket No.: 50090-449

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

4/30/03

In re Application of

Takashi TERAUCHI, et al.

Serial No.: 09/976,341

Group Art Unit: 2812

Filed: October 15, 2001

Examiner: R.E. Pompey

For: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, AND SEMICONDUCTOR DEVICE HAVING MEMORY CELL

RECEIVED APR 29 2003 TECHNOLOGY CENTER 2800

AMENDMENT

Commissioner for Patents
Washington, DC 20231

Sir:

The following Amendments and Remarks are submitted in response to the Office Action dated January 28, 2003.

IN THE CLAIMS:

Please amend claims 1 and 6 as follows:

1. (Amended) A method of manufacturing a semiconductor device, comprising the steps of:

forming a gate oxide film on a substrate;

forming gate interconnections on the gate oxide film, each gate interconnection including a first silicon film, forming an interface with an upper surface of the gate oxide film, and a dielectric film;